

II. This is in response to the final Office Action dated September 11, 2002, the period for reply having been extended by the above petition and payment of the extension fee. Please amend the above-identified application under 37 C.F.R. §1.116, as follows and consider the following remarks.

IN THE CLAIMS:

Please cancel claims 14-26 without prejudice or disclaimer.

Please amend claims 1, ~~6~~^{AC} and 11-13 as follows. A marked-up copy of the claims, showing the changes made thereto, is attached.

1. (Twice Amended) A deposited-film formation method comprising

the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust

means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma

CVD,

wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, and a periodically changing voltage having a voltage frequency of 1 MHz to 500 MHz and

*PF
conc
CVD*

a maximum amplitude of 80V or less is applied to the auxiliary electrode to form a deposited film while controlling generation of hydrogen radicals.

11. (Twice Amended) A deposited-film formation method comprising

the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, a periodically changing voltage having a voltage frequency of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode so that a voltage lower than the potential of plasma from the material gas is applied only in a certain period in at least one cycle of the periodically changing voltage, thereby forming a deposited film and controlling generation of hydrogen radicals.

12. (Twice Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power to the discharge electrode; and

forming a deposited film on a substrate in the vacuum vessel by plasma CVD,

wherein an auxiliary electrode is arranged in plasma in the vacuum vessel, a high-frequency power of 1 MHz to 200 MHz is applied to the discharge electrode, and a high-frequency power of 1 MHz to 500 MHz and a maximum amplitude of 80V or less is applied to the auxiliary electrode, thereby forming a deposited film and controlling generation of hydrogen radicals.

13. (Twice Amended) A deposited-film formation method comprising the steps of:

providing a discharge electrode in a vacuum vessel equipped with exhaust means;

supplying a hydrogen gas and a raw material gas for forming a deposited film which contains at least an Si element;

generating plasma from the material gas by supplying high frequency electric power of 1 MHz to 200 MHz to the discharge electrode; and